Welcome to E-XFL.COM

Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

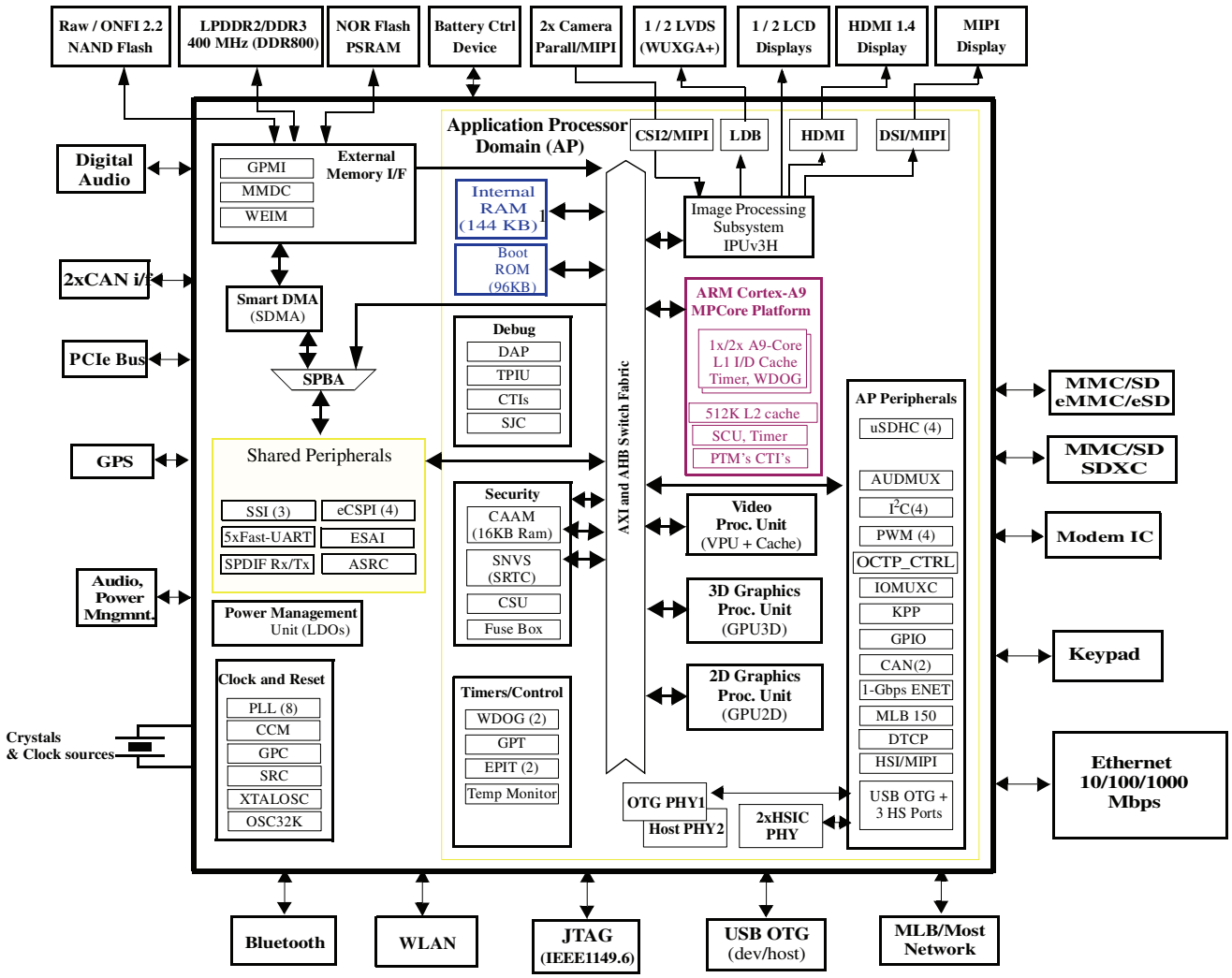
Details	
Product Status	Active
Core Processor	ARM® Cortex®-A9
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	800MHz
Co-Processors/DSP	Multimedia; NEON™ SIMD
RAM Controllers	LPDDR2, LVDDR3, DDR3
Graphics Acceleration	Yes
Display & Interface Controllers	Keypad, LCD
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 2.0 + PHY (4)
Voltage - I/O	1.8V, 2.5V, 2.8V, 3.3V
Operating Temperature	-40°C ~ 125°C (TJ)
Security Features	ARM TZ, Boot Security, Cryptography, RTIC, Secure Fusebox, Secure JTAG, Secure Memory, Secure RTC, Tamper Detection
Package / Case	624-LFBGA
Supplier Device Package	624-MAPBGA (21x21)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mcimx6s4avm08abr

2 Architectural Overview

The following subsections provide an architectural overview of the i.MX 6Solo/6DualLite processor system.

2.1 Block Diagram

Figure 2 shows the functional modules in the i.MX 6Solo/6DualLite processor system.



1 144 KB RAM including 16 KB RAM inside the CAAM.

2 For i.MX 6Solo, there is only one A9-core platform in the chip; for i.MX 6DualLite, there are two A9-core platforms.

Figure 2. i.MX 6Solo/6DualLite System Block Diagram

Table 7. Absolute Maximum Ratings (continued)

Parameter Description	Symbol	Min	Max	Unit
ESD damage immunity: • Human Body Model (HBM) • Charge Device Model (CDM)	V_{esd}	 — —	 2000 500	V
Storage temperature range	$T_{STORAGE}$	-40	150	°C

1 OVDD is the I/O supply voltage.

4.1.2 Thermal Resistance

4.1.2.1 BGA Case 2240 Package Thermal Resistance

Table 8 displays the thermal resistance data.

Table 8. Thermal Resistance Data

Rating	Test Conditions	Symbol	Value	Unit
Junction to Ambient[1]	Single-layer board (1s); natural convection[2] Four-layer board (2s2p); natural convection[2]	$R_{\theta JA}$ $R_{\theta JA}$	38 23	°C/W °C/W
Junction to Ambient[1]	Single-layer board (1s); airflow 200 ft/min[2,3] Four-layer board (2s2p); airflow 200 ft/min[2,3]	$R_{\theta JA}$ $R_{\theta JA}$	30 20	°C/W °C/W
Junction to Board[1,4]		$R_{\theta JB}$	14	°C/W
Junction to Case[1,5]		$R_{\theta JC}$	6	°C/W
Junction to Package Top[1,6]	Natural Convection	Ψ_{JT}	2	°C/W

1 Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

2 Per JEDEC JESD51-2 with the single layer board horizontal. Thermal test board meets JEDEC specification for the specified package.

3 Per JEDEC JESD51-6 with the board horizontal.

4 Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.

5 Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).

6 Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

Table 9. Operating Ranges (continued)

Parameter Description	Symbol	Min	Typ	Max[1]	Unit	Comment
GPIO supply voltages[6]	NVCC_CSI, NVCC_EIM, NVCC_ENET, NVCC_GPIO, NVCC_LCD, NVCC_NANDF, NVCC_SD1, NVCC_SD2, NVCC_SD3, NVCC_JTAG	1.65	1.8, 2.8, 3.3	3.6	V	
	NVCC_LVDS2P5[7] NVCC_MIPI	2.25	2.5	2.75	V	
HDMI supply voltages	HDMI_VP	0.99	1.1	1.3	V	
	HDMI_VPH	2.25	2.5	2.75	V	
PCIe supply voltages	PCIE_VP	1.023	1.1	1.225	V	
	PCIE_VPH	2.325	2.5	2.75	V	
	PCIE_VPTX	1.023	1.1	1.225	V	
Junction temperature	T_J	-40	—	125	°C	Refer to Automotive qualification report for details.

1 Applying the maximum voltage results in maximum power consumption and heat generation. Freescale recommends a voltage set point = (Vmin + the supply tolerance). This results in an optimized power/speed ratio.

2 VDDARM_IN and VDDSOC_IN must be 125 mV higher than the LDO Output Set Point for correct regulator supply voltage.

3 VDDSOC_CAP and VDDPU_CAP must be equal.

4 VDDSOC and VDDPU output voltage must be set to this rule: VDDARM - VDDSOC/PU < 100 mV.

5 While setting VDD_SNVS_IN voltage with respect to Charging Currents and RTC, refer to Hardware Development Guide for i.MX 6Dual, 6Quad, 6Solo, 6DualLite Families of Applications Processors (IMX6DQ6SDLHDG).

6 All digital I/O supplies (NVCC_xxxx) must be powered under normal conditions whether the associated I/O pins are in use or not and associated IO pins need to have a Pullup or Pulldown resistor applied to limit any floating gate current.

7 This supply also powers the pre-drivers of the DDR IO pins, hence, it must be always provided, even when LVDS is not used

Table 10 shows on-chip LDO regulators that can supply on-chip loads.

Table 10. On-Chip LDOs[1] and their On-Chip Loads

Voltage Source	Load	Comment
VDDHIGH_CAP	NVCC_LVDS2P5	Board-level connection to VDDHIGH_CAP
	NVCC_MIPI	
	HDMI_VPH	
	PCIE_VPH	

4.1.9 HDMI Power Consumption

Table 16 provides HDMI PHY currents for both Active 3D Tx with LFSR15 data and power-down modes.

Table 16. HDMI PHY Current Drain

Mode	Test Conditions	Supply	Max Current	Unit
Active	Bit rate 251.75 Mbps	HDMI_VPH	14	mA
		HDMI_VP	4.1	mA
	Bit rate 279.27 Mbps	HDMI_VPH	14	mA
		HDMI_VP	4.2	mA
	Bit rate 742.5 Mbps	HDMI_VPH	17	mA
		HDMI_VP	7.5	mA
	Bit rate 1.485 Gbps	HDMI_VPH	17	mA
		HDMI_VP	12	mA
	Bit rate 2.275 Gbps	HDMI_VPH	16	mA
		HDMI_VP	17	mA
	Bit rate 2.97 Gbps	HDMI_VPH	19	mA
		HDMI_VP	22	mA
Power-down		HDMI_VPH	49	µA
		HDMI_VP	1100	µA

4.2 Power Supplies Requirements and Restrictions

The system design must comply with power-up sequence, power-down sequence, and steady state guidelines as described in this section to guarantee the reliable operation of the device. Any deviation from these sequences may result in the following situations:

- Excessive current during power-up phase
- Prevention of the device from booting
- Irreversible damage to the processor (worst-case scenario)

4.2.1 Power-Up Sequence

The below restrictions must be followed:

- VDD_SNVS_IN supply must be turned on before any other power supply or be connected (shorted) with VDDHIGH_IN supply.
- If a coin cell is used to power VDD_SNVS_IN, then ensure that it is connected before any other supply is switched on.
- If VDDARM_IN and VDDSOC_IN are connected to different external supply sources, then the following restrictions apply:

their input supply ripple rejection and their on-die trimming. This translates into more stable voltage for the on-chip logics.

These regulators have three basic modes:

- Bypass. The regulation FET is switched fully on passing the external voltage, to the load unaltered. The analog part of the regulator is powered down in this state, removing any loss other than the IR drop through the power grid and FET.
- Power Gate. The regulation FET is switched fully off limiting the current draw from the supply. The analog part of the regulator is powered down here limiting the power consumption.
- Analog regulation mode. The regulation FET is controlled such that the output voltage of the regulator equals the programmed target voltage. The target voltage is fully programmable in 25 mV steps.

For additional information, see the i.MX 6Solo/6DualLite reference manual.

4.3.2 Analog Regulators

4.3.2.1 LDO_1P1

The LDO_1P1 regulator implements a programmable linear-regulator function from VDDHIGH_IN (see Table 9 for minimum and maximum input requirements). Typical Programming Operating Range is 1.0 V to 1.2 V with the nominal default setting as 1.1 V. Since the accuracy or the % regulation is not tested, and only tested with the LDO set to either 1.0V or 1.2V, this is the only range that is guaranteed. The regulator has been designed to be stable with a minimum external low ESR decoupling capacitor of 1 µF (2.2 µF should be considered the recommended minimum value for component selection), though the actual capacitance required should be determined by the application. A programmable brown-out detector is included in the regulator that can be used by the system to determine when the load capability of the regulator is being exceeded to take the necessary steps. Current-limiting can be enabled to allow for in-rush current requirements during start-up, if needed. Active-pull-down can also be enabled for systems requiring this feature.

For additional information, see the i.MX 6Solo/6DualLite reference manual.

4.3.2.2 LDO_2P5

The LDO_2P5 module implements a programmable linear-regulator function from VDDHIGH_IN (see Table 9 for minimum and maximum input requirements). Typical Programming Operating Range is 2.25 V to 2.75 V with the nominal default setting as 2.5 V. Since the accuracy or the % regulation is not tested, and only tested with the LDO set to either 2.25V or 2.75V, this is the only range that is guaranteed. The regulator has been designed to be stable with a minimum external low ESR decoupling capacitor of 1 µF (2.2 µF should be considered the recommended minimum value for component selection), though the actual capacitance required should be determined by the application. A programmable brown-out detector is included in the regulator that can be used by the system to determine when the load capability of the regulator is being exceeded, to take the necessary steps. Current-limiting can be enabled to allow for in-rush current requirements during start-up, if needed. Active-pull-down can also be enabled for systems requiring this feature. An alternate self-biased low-precision weak-regulator is included that can be

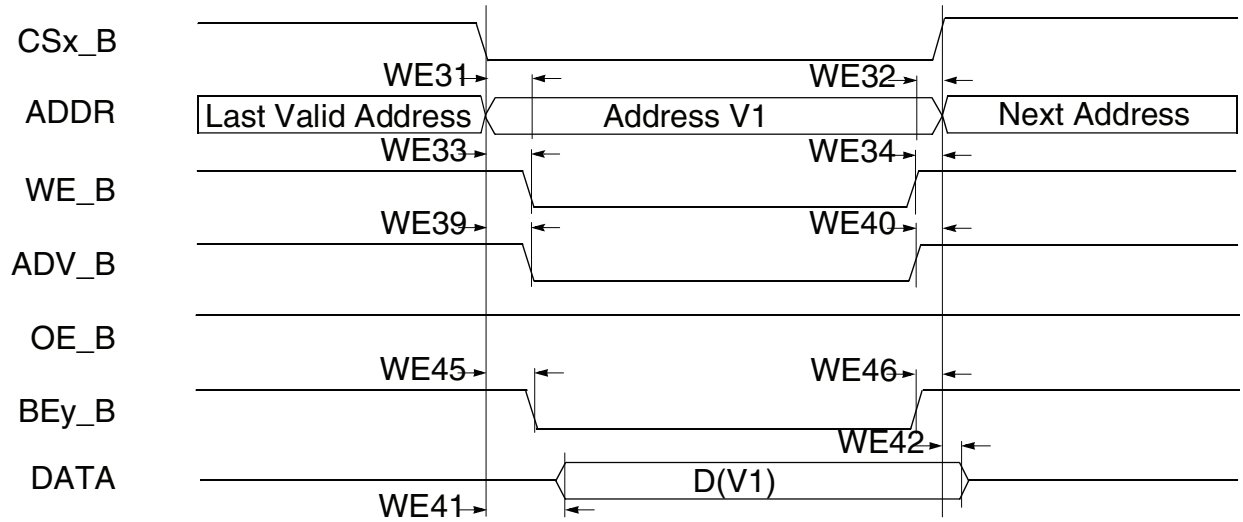


Figure 20. Asynchronous Memory Write Access

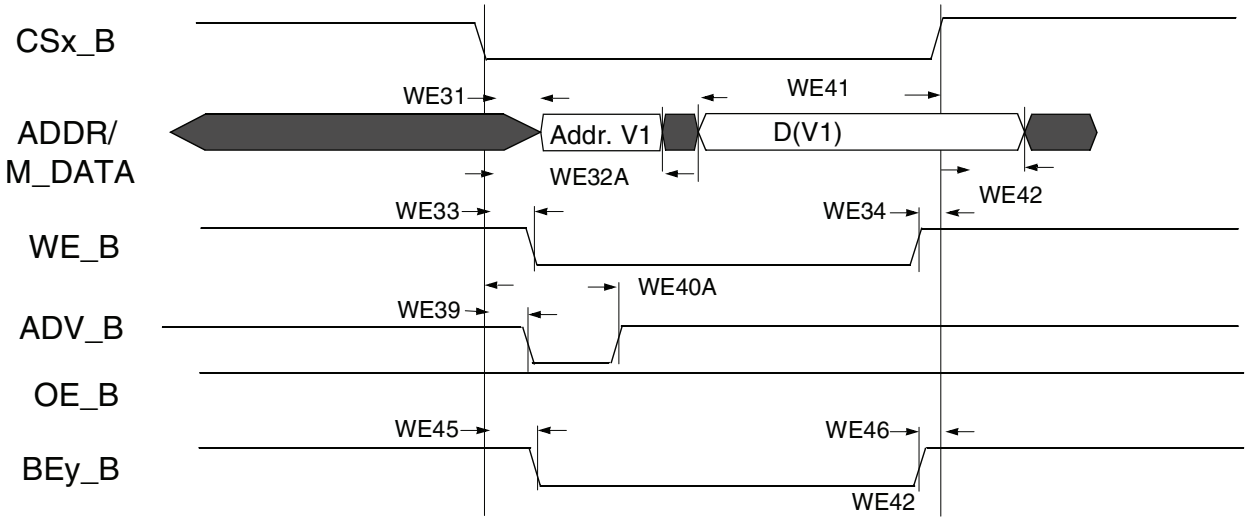


Figure 21. Asynchronous A/D Muxed Write Access

4.9.4 DDR SDRAM Specific Parameters (DDR3/DDR3L and LPDDR2)

4.9.4.1 DDR3/DDR3L Parameters

Figure 24 shows the basic timing parameters. The timing parameters for this diagram appear in Table 45.

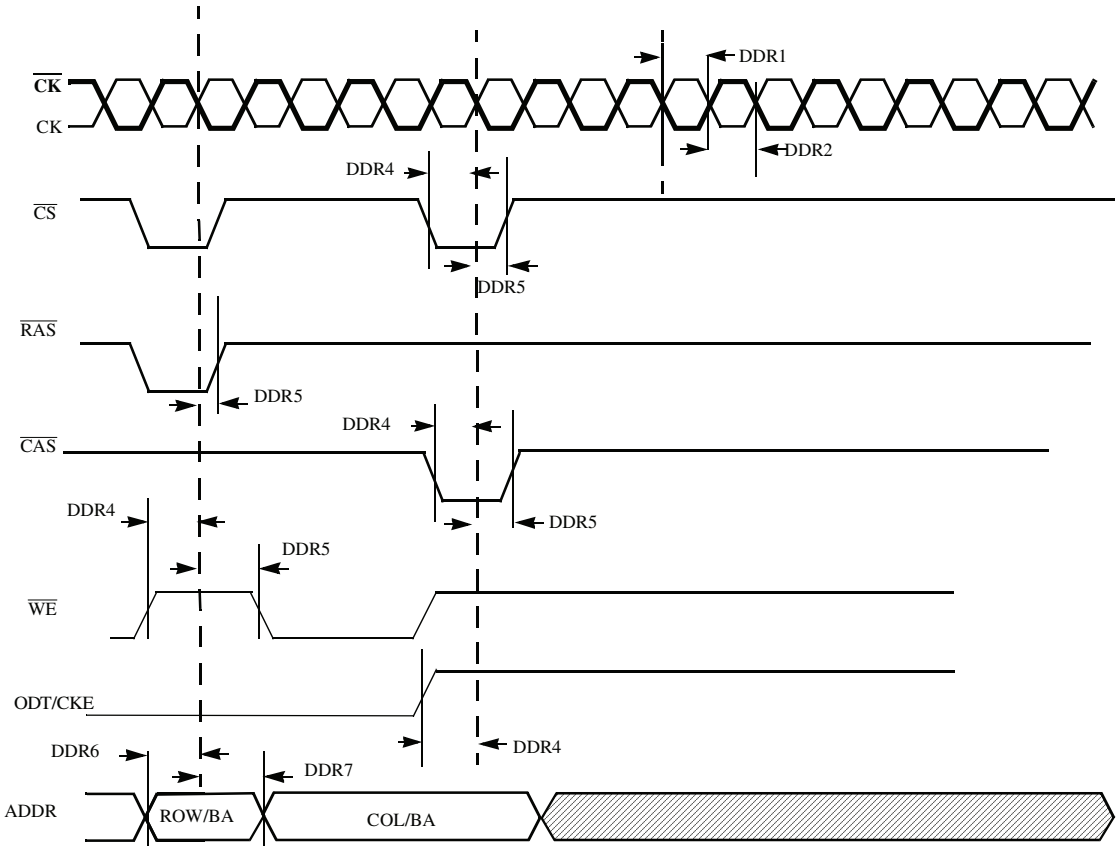


Figure 24. DDR3 Command and Address Timing Parameters

Table 45. DDR3/DDR3L Timing Parameter Table

ID	Parameter	Symbol	CK = 400 MHz		Unit
			Min	Max	
DDR1	CK clock high-level width	t_{CH}	0.47	0.53	t_{CK}
DDR2	CK clock low-level width	t_{CL}	0.47	0.53	t_{CK}
DDR4	CS, RAS, CAS, CKE, WE, ODT setup time	t_{IS}	800	—	ps
DDR5	CS, RAS, CAS, CKE, WE, ODT hold time	t_{IH}	580	—	ps
DDR6	Address output setup time	t_{IS}	800	—	ps
DDR7	Address output hold time	t_{IH}	580	—	ps

Figure 28 shows the write timing parameters. The timing parameters for this diagram appear in Table 49.

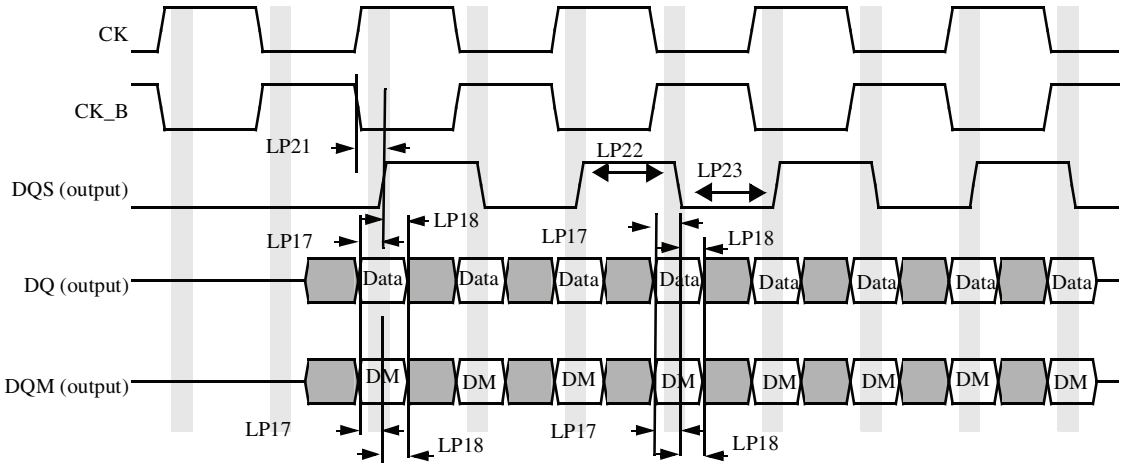


Figure 28. LPDDR2 Write Cycle

Table 49. LPDDR2 Write Cycle

ID	Parameter	Symbol	CK = 400 MHz		Unit
			Min	Max	
LP17	DQ and DQM setup time to DQS (differential strobe)	t_{DS}	375	—	ps
LP18	DQ and DQM hold time to DQS (differential strobe)	t_{DH}	375	—	ps
LP21	DQS latching rising transitions to associated clock edges	t_{DQSS}	-0.25	+0.25	tCK
LP22	DQS high level width	t_{DQSH}	0.4	-	tCK
LP23	DQS low level width	t_{DQSL}	0.4	-	tCK

1 To receive the reported setup and hold values, write calibration should be performed in order to locate the DQS in the middle of DQ window.

2 All measurements are in reference to Vref level.

3 Measurements were done using balanced load and 25 Ω resistor from outputs to VDD_REF.

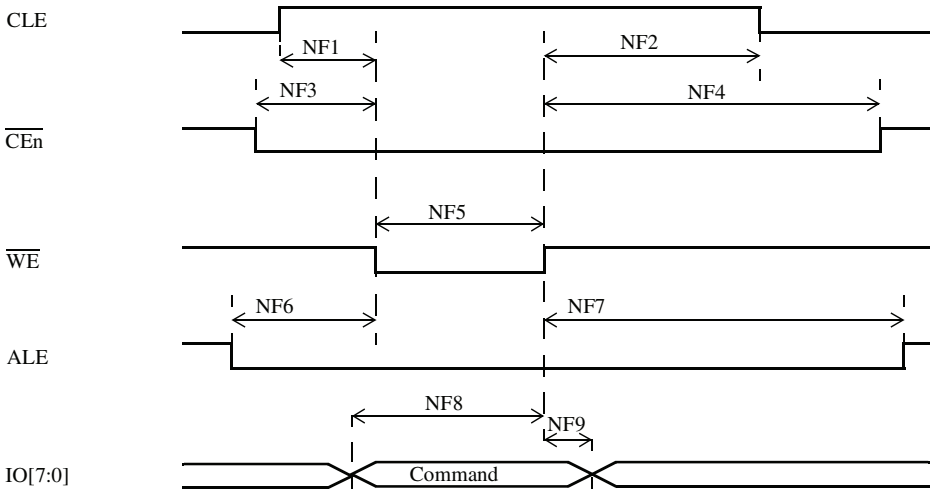


Figure 30. Command Latch Cycle Timing Diagram

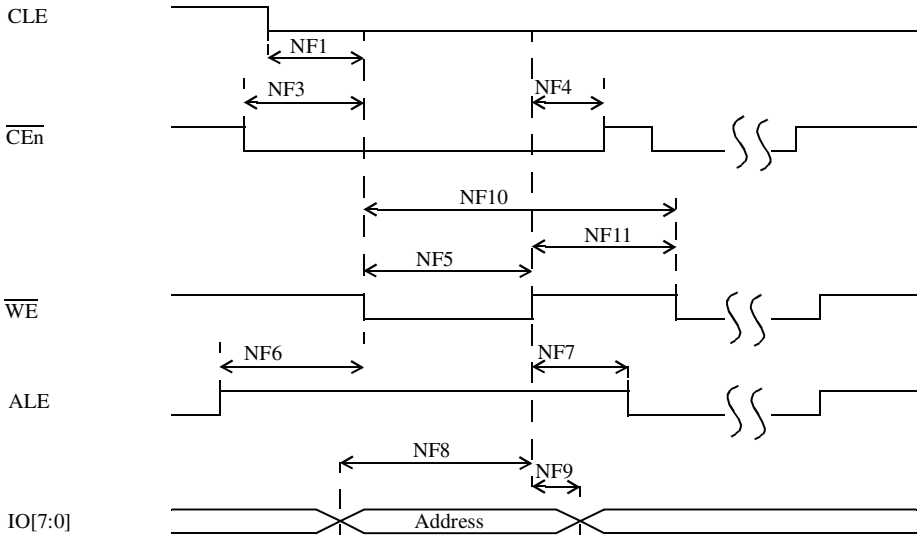


Figure 31. Address Latch Cycle Timing Diagram

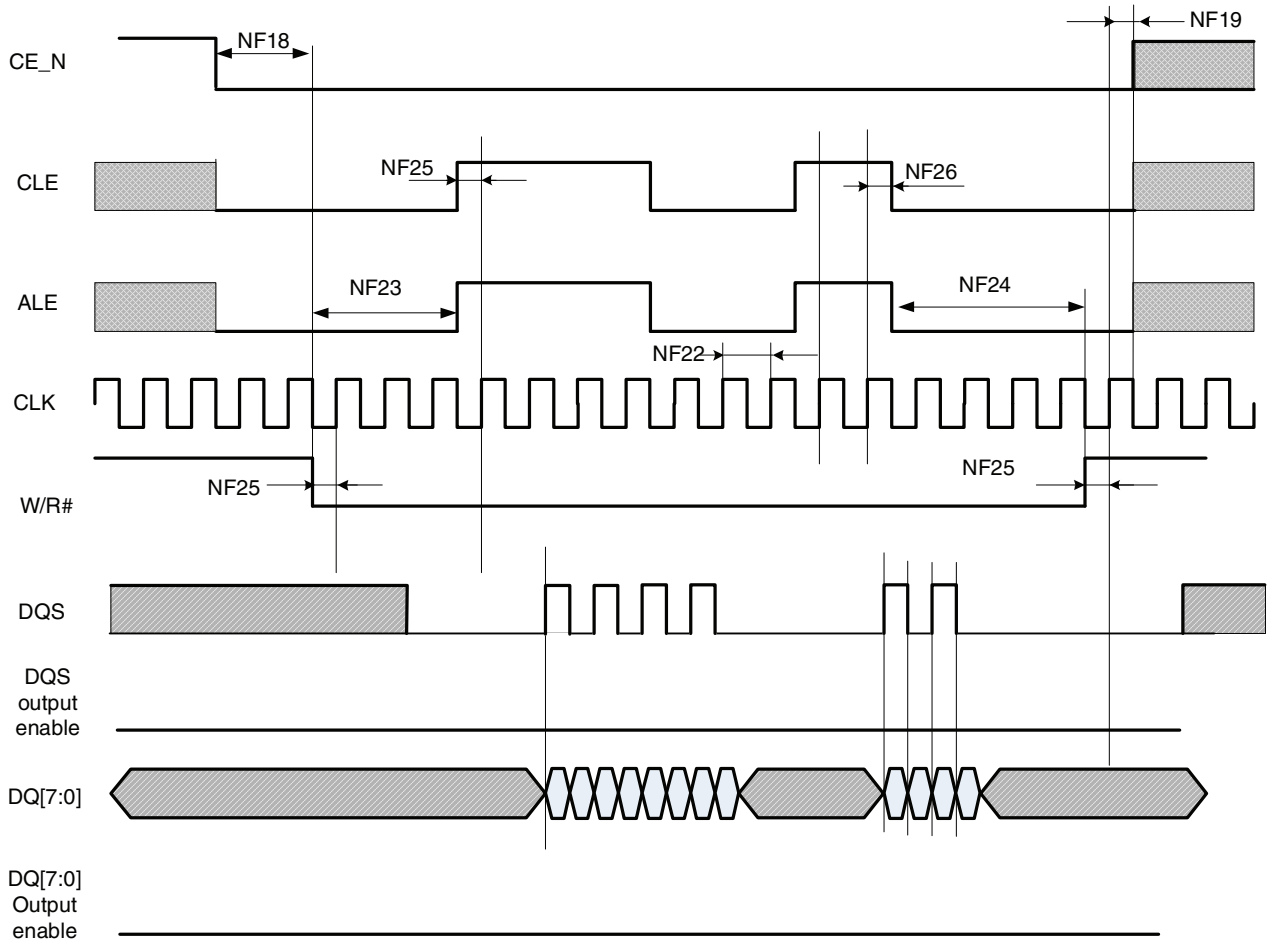


Figure 36. Source Synchronous Mode Data Read Timing Diagram

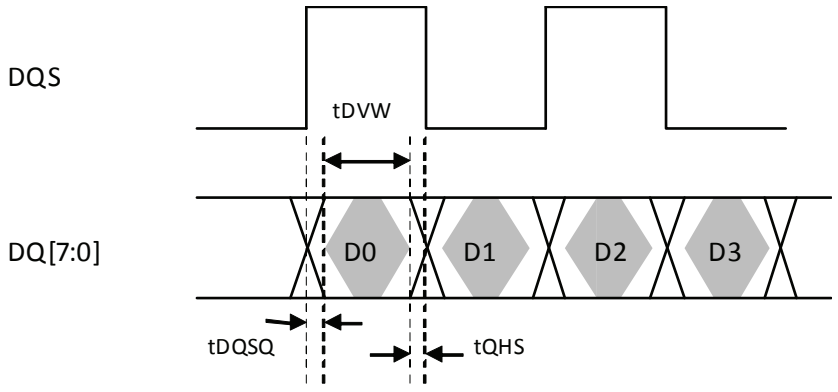


Figure 37. DQS/DQ Read Valid Window

Table 56. Enhanced Serial Audio Interface (ESAI) Timing (continued)

No.	Characteristics[1,2]	Symbol	Expression[2]	Min	Max	Condition[3]	Unit
81	SCKT rising edge to FST out (wr) low[5]	— —	— —	— —	22.0 12.0	x ck i ck	ns
82	SCKT rising edge to FST out (wl) high	— —	— —	— —	19.0 9.0	x ck i ck	ns
83	SCKT rising edge to FST out (wl) low	— —	— —	— —	20.0 10.0	x ck i ck	ns
84	SCKT rising edge to data out enable from high impedance	— —	— —	— —	22.0 17.0	x ck i ck	ns
86	SCKT rising edge to data out valid	— —	— —	— —	18.0 13.0	x ck i ck	ns
87	SCKT rising edge to data out high impedance [67]	— —	— —	— —	21.0 16.0	x ck i ck	ns
89	FST input (bl, wr) setup time before SCKT falling edge[5]	— —	— —	2.0 18.0	— —	x ck i ck	ns
90	FST input (wl) setup time before SCKT falling edge	— —	— —	2.0 18.0	— —	x ck i ck	ns
91	FST input hold time after SCKT falling edge	— —	— —	4.0 5.0	— —	x ck i ck	ns
95	HCKR/HCKT clock cycle	—	2 x T_C	15	—	—	ns
96	HCKT input rising edge to SCKT output	—	—	—	18.0	—	ns
97	HCKR input rising edge to SCKR output	—	—	—	18.0	—	ns

1 i ck = internal clock
x ck = external clock
i ck a = internal clock, asynchronous mode
(asynchronous implies that SCKT and SCKR are two different clocks)
i ck s = internal clock, synchronous mode
(synchronous implies that SCKT and SCKR are the same clock)

2 bl = bit length
wl = word length
wr = word length relative

3 SCKT(SCKT pin) = transmit clock
SCKR(SCKR pin) = receive clock
FST(FST pin) = transmit frame sync
FSR(FSR pin) = receive frame sync
HCKT(HCKT pin) = transmit high frequency clock
HCKR(HCKR pin) = receive high frequency clock

4 For the internal clock, the external clock cycle is defined by Icyc and the ESAI control register.

5 The word-relative frame sync signal waveform relative to the clock operates in the same manner as the bit-length frame sync signal waveform, but it spreads from one serial clock before the first bit clock (like the bit length frame sync signal), until the second-to-last bit clock of the first word in the frame.

6 Periodically sampled and not 100% tested.

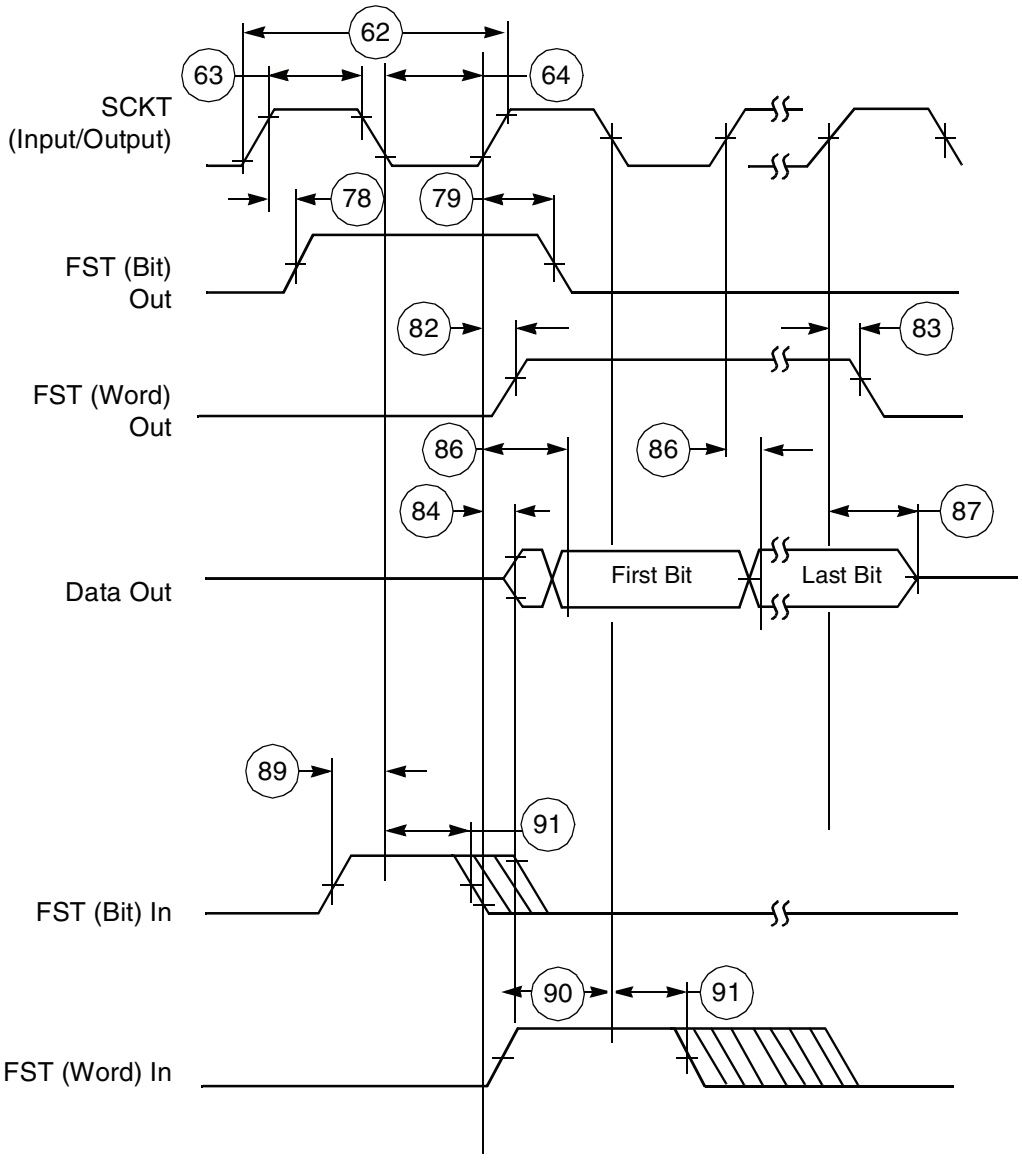


Figure 42. ESAI Transmitter Timing

4.11.5.1.4 MII Serial Management Channel Timing (ENET_MDIO and ENET_MDC)

The MDC frequency is designed to be equal to or less than 2.5 MHz to be compatible with the IEEE 802.3 MII specification. However the ENET can function correctly with a maximum MDC frequency of 15 MHz.

Figure 50 shows MII asynchronous input timings. Table 63 describes the timing parameters (M10–M15) shown in the figure.

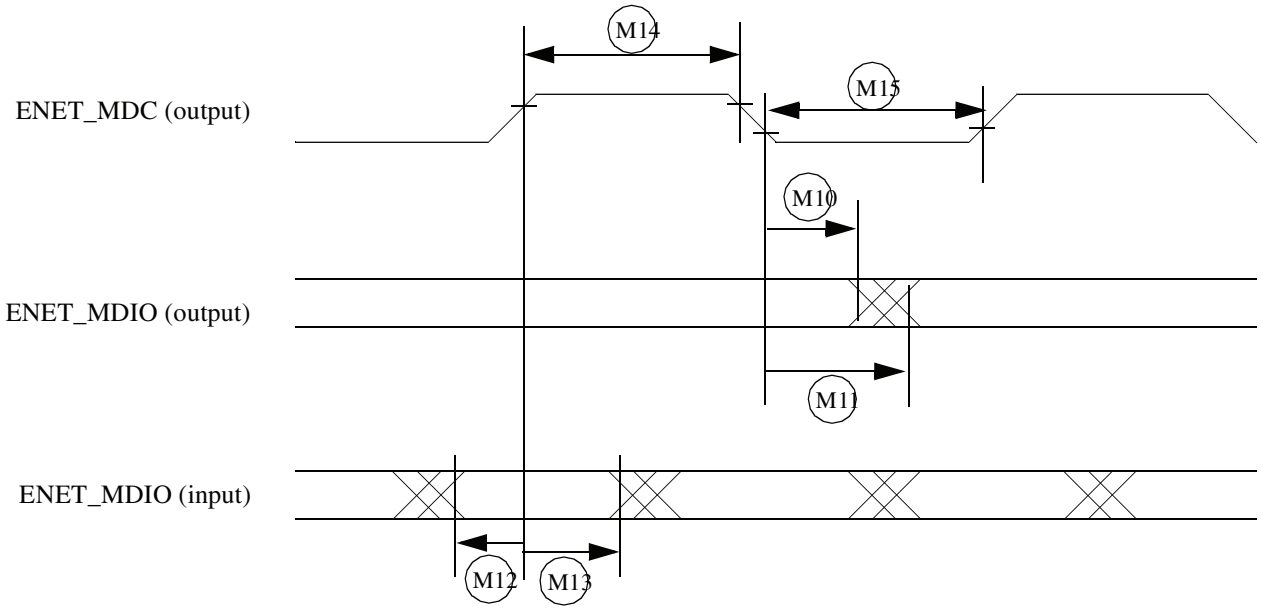


Figure 50. MII Serial Management Channel Timing Diagram

Table 63. MII Serial Management Channel Timing

ID	Characteristic	Min.	Max.	Unit
M10	ENET_MDC falling edge to ENET_MDIO output invalid (min. propagation delay)	0	—	ns
M11	ENET_MDC falling edge to ENET_MDIO output valid (max. propagation delay)	—	5	ns
M12	ENET_MDIO (input) to ENET_MDC rising edge setup	18	—	ns
M13	ENET_MDIO (input) to ENET_MDC rising edge hold	0	—	ns
M14	ENET_MDC pulse width high	40%	60%	ENET_MDC period
M15	ENET_MDC pulse width low	40%	60%	ENET_MDC period

4.11.5.2 RMII Mode Timing

In RMII mode, ENET_CLK is used as the REF_CLK, which is a 50 MHz ± 50 ppm continuous reference clock. ENET_RX_EN is used as the CRS_DV in RMII. Other signals under RMII mode include ENET_TX_EN, ENET0_TXD[1:0], ENET0_RXD[1:0] and ENET_RX_ER.

4.11.10.6.3 TFT Panel Sync Pulse Timing Diagrams

Figure 68 depicts the horizontal timing (timing of one line), including both the horizontal sync pulse and the data. All the parameters shown in the figure are programmable. All controls are started by corresponding internal events—local start points. The timing diagrams correspond to inverse polarity of the IPP_DISP_CLK signal and active-low polarity of the HSYNC, VSYNC, and DRDY signals.

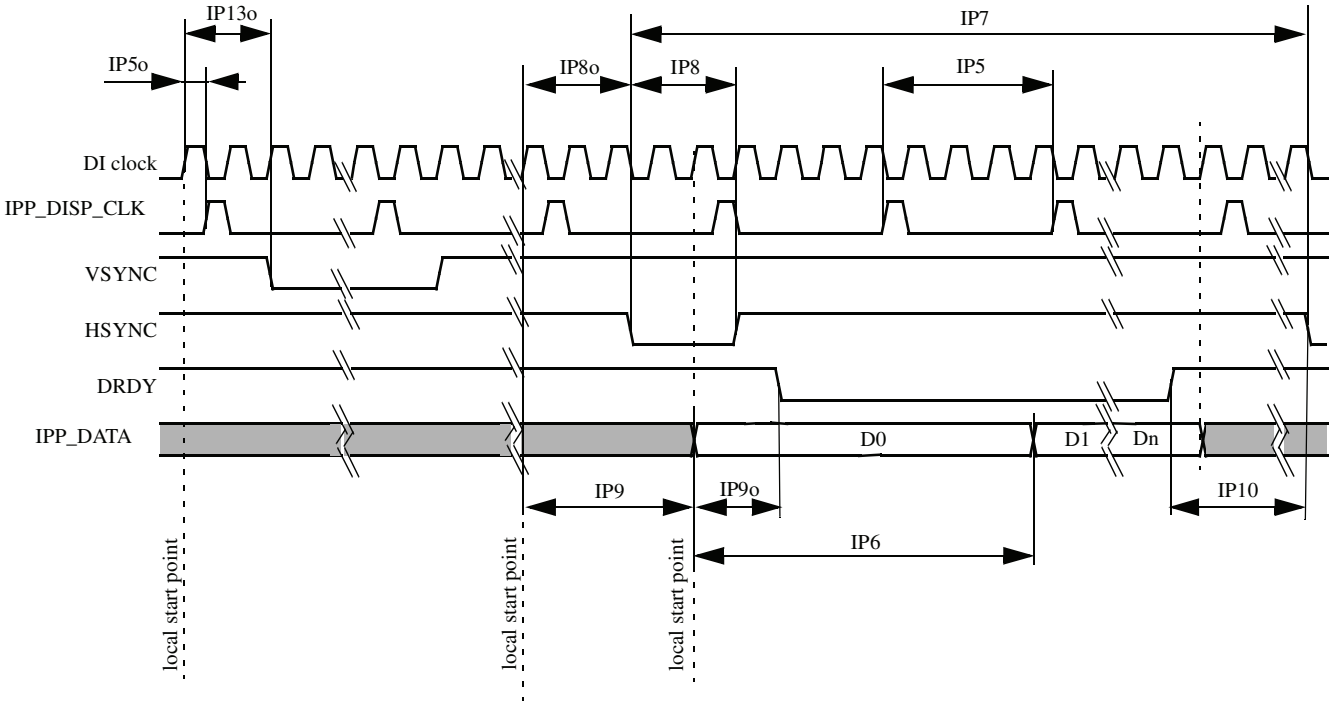


Figure 68. TFT Panels Timing Diagram—Horizontal Sync Pulse

Figure 69 depicts the vertical timing (timing of one frame). All parameters shown in the figure are programmable.

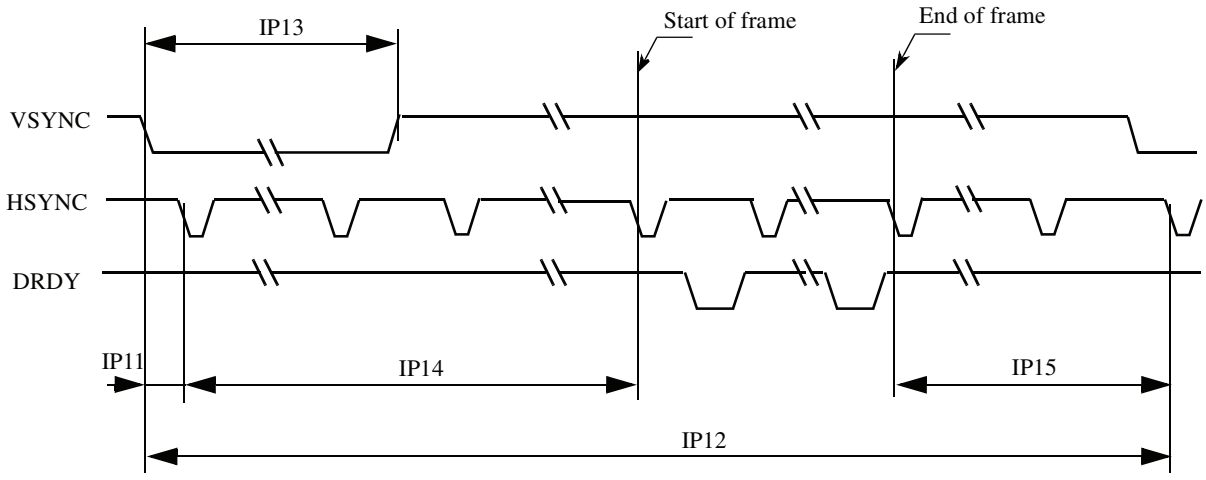


Figure 69. TFT Panels Timing Diagram—Vertical Sync Pulse

Table 87. SSI Transmitter Timing with Internal Clock (continued)

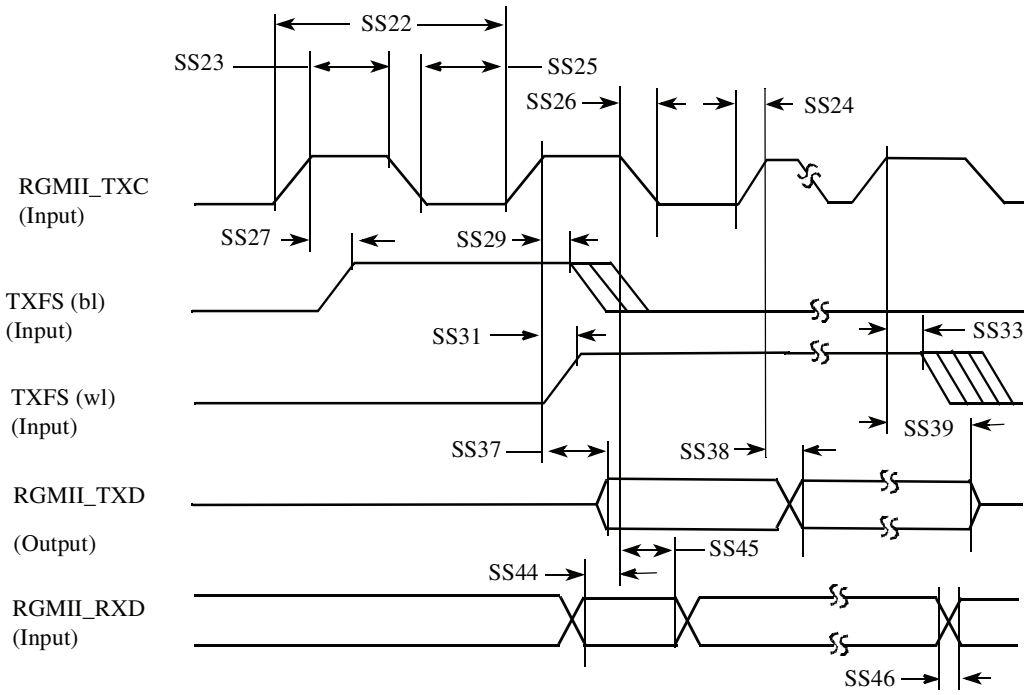
ID	Parameter	Min	Max	Unit
Synchronous Internal Clock Operation				
SS42	SRXD setup before (Tx) CK falling	10.0	—	ns
SS43	SRXD hold after (Tx) CK falling	0.0	—	ns

NOTE

- All the timings for the SSI are given for a non-inverted serial clock polarity (TSCKP/RSCKP = 0) and a non-inverted frame sync (TFSI/RFSI = 0). If the polarity of the clock and/or the frame sync have been inverted, all the timing remains valid by inverting the clock signal STCK/SRCK and/or the frame sync STFS/SRFS shown in the tables and in the figures.
- All timings are on Audiomux Pads when SSI is being used for data transfer.
- The terms, WL and BL, refer to Word Length (WL) and Bit Length (BL).
- “Tx” and “Rx” refer to the Transmit and Receive sections of the SSI.
- For internal Frame Sync operation using external clock, the FS timing is same as that of Tx Data (for example, during AC97 mode of operation).

4.11.19.3 SSI Transmitter Timing with External Clock

Figure 97 depicts the SSI transmitter external clock timing and Table 89 lists the timing parameters for the transmitter timing with the external clock.



Note: SRXD Input in Synchronous mode only

Figure 97. SSI Transmitter External Clock Timing Diagram

Table 89. SSI Transmitter Timing with External Clock

ID	Parameter	Min	Max	Unit
External Clock Operation				
SS22	(Tx/Rx) CK clock period	81.4	—	ns
SS23	(Tx/Rx) CK clock high period	36.0	—	ns
SS24	(Tx/Rx) CK clock rise time	—	6.0	ns
SS25	(Tx/Rx) CK clock low period	36.0	—	ns
SS26	(Tx/Rx) CK clock fall time	—	6.0	ns
SS27	(Tx) CK high to FS (bl) high	-10.0	15.0	ns
SS29	(Tx) CK high to FS (bl) low	10.0	—	ns
SS31	(Tx) CK high to FS (wl) high	-10.0	15.0	ns
SS33	(Tx) CK high to FS (wl) low	10.0	—	ns
SS37	(Tx) CK high to STXD valid from high impedance	—	15.0	ns
SS38	(Tx) CK high to STXD high/low	—	15.0	ns

Table 101. 21 x 21 mm Functional Contact Assignments[1] (continued)

Ball Name	Ball	Power Group	Ball Type	Out of Reset Condition[2]			
				Default Mode (Reset Mode)	Default Function	Input/ Output	Value
DISP0_DAT3	P21	NVCC_LCD	GPIO	ALT5	gpio4.GPIO[24]	Input	100 kΩ pull-up
DISP0_DAT4	P20	NVCC_LCD	GPIO	ALT5	gpio4.GPIO[25]	Input	100 kΩ pull-up
DISP0_DAT5	R25	NVCC_LCD	GPIO	ALT5	gpio4.GPIO[26]	Input	100 kΩ pull-up
DISP0_DAT6	R23	NVCC_LCD	GPIO	ALT5	gpio4.GPIO[27]	Input	100 kΩ pull-up
DISP0_DAT7	R24	NVCC_LCD	GPIO	ALT5	gpio4.GPIO[28]	Input	100 kΩ pull-up
DISP0_DAT8	R22	NVCC_LCD	GPIO	ALT5	gpio4.GPIO[29]	Input	100 kΩ pull-up
DISP0_DAT9	T25	NVCC_LCD	GPIO	ALT5	gpio4.GPIO[30]	Input	100 kΩ pull-up
DRAM_A0	AC14	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[0]	Output	Low
DRAM_A1	AB14	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[1]	Output	Low
DRAM_A10	AA15	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[10]	Output	Low
DRAM_A11	AC12	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[11]	Output	Low
DRAM_A12	AD12	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[12]	Output	Low
DRAM_A13	AC17	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[13]	Output	Low
DRAM_A14	AA12	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[14]	Output	Low
DRAM_A15	Y12	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[15]	Output	Low
DRAM_A2	AA14	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[2]	Output	Low
DRAM_A3	Y14	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[3]	Output	Low
DRAM_A4	W14	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[4]	Output	Low
DRAM_A5	AE13	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[5]	Output	Low
DRAM_A6	AC13	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[6]	Output	Low
DRAM_A7	Y13	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[7]	Output	Low
DRAM_A8	AB13	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[8]	Output	Low
DRAM_A9	AE12	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_A[9]	Output	Low
DRAM_CAS	AE16	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_CAS	Output	Low
DRAM_CS0	Y16	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_CS[0]	Output	Low
DRAM_CS1	AD17	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_CS[1]	Output	Low
DRAM_D0	AD2	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[0]	Input	100 kΩ pull-up
DRAM_D1	AE2	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[1]	Input	100 kΩ pull-up
DRAM_D10	AA6	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[10]	Input	100 kΩ pull-up
DRAM_D11	AE7	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[11]	Input	100 kΩ pull-up

Table 101. 21 x 21 mm Functional Contact Assignments[1] (continued)

Ball Name	Ball	Power Group	Ball Type	Out of Reset Condition[2]			
				Default Mode (Reset Mode)	Default Function	Input/ Output	Value
DRAM_D4	AC1	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[4]	Input	100 kΩ pull-up
DRAM_D40	Y19	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[40]	Input	100 kΩ pull-up
DRAM_D41	AB20	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[41]	Input	100 kΩ pull-up
DRAM_D42	AB21	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[42]	Input	100 kΩ pull-up
DRAM_D43	AD21	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[43]	Input	100 kΩ pull-up
DRAM_D44	Y20	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[44]	Input	100 kΩ pull-up
DRAM_D45	AA20	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[45]	Input	100 kΩ pull-up
DRAM_D46	AE21	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[46]	Input	100 kΩ pull-up
DRAM_D47	AC21	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[47]	Input	100 kΩ pull-up
DRAM_D48	AC22	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[48]	Input	100 kΩ pull-up
DRAM_D49	AE22	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[49]	Input	100 kΩ pull-up
DRAM_D5	AD1	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[5]	Input	100 kΩ pull-up
DRAM_D50	AE24	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[50]	Input	100 kΩ pull-up
DRAM_D51	AC24	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[51]	Input	100 kΩ pull-up
DRAM_D52	AB22	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[52]	Input	100 kΩ pull-up
DRAM_D53	AC23	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[53]	Input	100 kΩ pull-up
DRAM_D54	AD25	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[54]	Input	100 kΩ pull-up
DRAM_D55	AC25	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[55]	Input	100 kΩ pull-up
DRAM_D56	AB25	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[56]	Input	100 kΩ pull-up
DRAM_D57	AA21	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[57]	Input	100 kΩ pull-up
DRAM_D58	Y25	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[58]	Input	100 kΩ pull-up
DRAM_D59	Y22	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[59]	Input	100 kΩ pull-up
DRAM_D6	AB4	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[6]	Input	100 kΩ pull-up
DRAM_D60	AB23	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[60]	Input	100 kΩ pull-up
DRAM_D61	AA23	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[61]	Input	100 kΩ pull-up
DRAM_D62	Y23	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[62]	Input	100 kΩ pull-up
DRAM_D63	W25	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[63]	Input	100 kΩ pull-up
DRAM_D7	AE4	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[7]	Input	100 kΩ pull-up
DRAM_D8	AD5	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[8]	Input	100 kΩ pull-up
DRAM_D9	AE5	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_D[9]	Input	100 kΩ pull-up

Table 101. 21 x 21 mm Functional Contact Assignments[1] (continued)

Ball Name	Ball	Power Group	Ball Type	Out of Reset Condition[2]			
				Default Mode (Reset Mode)	Default Function	Input/ Output	Value
DRAM_SDQS4_B	AE18	NVCC_DRAM			DRAM_SDQS4_B	-	-
DRAM_SDQS5	AD20	NVCC_DRAM	DDRCLK	ALT0	mmdc.DRAM_SDQS[5]	Input	Hi-Z
DRAM_SDQS5_B	AE20	NVCC_DRAM			DRAM_SDQS5_B	-	-
DRAM_SDQS6	AD23	NVCC_DRAM	DDRCLK	ALT0	mmdc.DRAM_SDQS[6]	Input	Hi-Z
DRAM_SDQS6_B	AE23	NVCC_DRAM			DRAM_SDQS6_B	-	-
DRAM_SDQS7	AA25	NVCC_DRAM	DDRCLK	ALT0	mmdc.DRAM_SDQS[7]	Input	Hi-Z
DRAM_SDQS7_B	AA24	NVCC_DRAM			DRAM_SDQS7_B	-	-
DRAM_SDWE	AB16	NVCC_DRAM	DDR	ALT0	mmdc.DRAM_SDWE	Output	Low
DSI_CLK0M	H3	NVCC_MIPI	ANALOG				
DSI_CLK0P	H4	NVCC_MIPI	ANALOG				
DSI_D0M	G2	NVCC_MIPI	ANALOG				
DSI_D0P	G1	NVCC_MIPI	ANALOG				
DSI_D1M	H2	NVCC_MIPI	ANALOG				
DSI_D1P	H1	NVCC_MIPI	ANALOG				
EIM_A16	H25	NVCC_EIM	GPIO	ALT0	weim.WEIM_A[16]	Output	Low
EIM_A17	G24	NVCC_EIM	GPIO	ALT0	weim.WEIM_A[17]	Output	Low
EIM_A18	J22	NVCC_EIM	GPIO	ALT0	weim.WEIM_A[18]	Output	Low
EIM_A19	G25	NVCC_EIM	GPIO	ALT0	weim.WEIM_A[19]	Output	Low
EIM_A20	H22	NVCC_EIM	GPIO	ALT0	weim.WEIM_A[20]	Output	Low
EIM_A21	H23	NVCC_EIM	GPIO	ALT0	weim.WEIM_A[21]	Output	Low
EIM_A22	F24	NVCC_EIM	GPIO	ALT0	weim.WEIM_A[22]	Output	Low
EIM_A23	J21	NVCC_EIM	GPIO	ALT0	weim.WEIM_A[23]	Output	Low
EIM_A24	F25	NVCC_EIM	GPIO	ALT0	weim.WEIM_A[24]	Output	Low
EIM_A25	H19	NVCC_EIM	GPIO	ALT0	weim.WEIM_A[25]	Output	Low
EIM_BCLK	N22	NVCC_EIM	GPIO	ALT0	weim.WEIM_BCLK	Output	Low
EIM_CS0	H24	NVCC_EIM	GPIO	ALT0	weim.WEIM_CS[0]	Output	High
EIM_CS1	J23	NVCC_EIM	GPIO	ALT0	weim.WEIM_CS[1]	Output	High
EIM_D16	C25	NVCC_EIM	GPIO	ALT5	gpio3.GPIO[16]	Input	100 kΩ pull-up
EIM_D17	F21	NVCC_EIM	GPIO	ALT5	gpio3.GPIO[17]	Input	100 kΩ pull-up
EIM_D18	D24	NVCC_EIM	GPIO	ALT5	gpio3.GPIO[18]	Input	100 kΩ pull-up

Table 103. 21 x 21 mm, 0.8 mm Pitch Ball Map (continued)

Y	W	V	U	T	R	P	N
LVDS1_TX0_N	LVDS0_TX3_P	LVDS0_TX2_P	LVDS0_TX0_P	GPIO_2	GPIO_17	CSI0_PIXCLK	CSI0_DAT4
LVDS1_TX0_P	LVDS0_TX3_N	LVDS0_TX2_N	LVDS0_TX0_N	GPIO_9	GPIO_16	CSI0_DAT5	CSI0_VSYNC
LVDS1_CLK_N	GND	LVDS0_CLK_P	LVDS0_TX1_P	GPIO_6	GPIO_7	CSI0_DATA_EN	CSI0_DAT7
LVDS1_CLK_P	KEY_ROW2	LVDS0_CLK_N	LVDS0_TX1_N	GPIO_1	GPIO_5	CSI0_MCLK	CSI0_DAT6
GND	KEY_COL0	KEY_ROW4	KEY_COL3	GPIO_0	GPIO_8	GPIO_19	CSI0_DAT9
DRAM_RESET	KEY_COL2	KEY_ROW0	KEY_ROW1	KEY_COL4	GPIO_4	GPIO_18	CSI0_DAT8
DRAM_D20	GND	NVCC_LVDS2P5	KEY_COL1	KEY_ROW3	GPIO_3	NVCC_GPIO	NVCC_CSI
DRAM_D21	GND	GND	GND	GND	GND	GND	GND
DRAM_D19	GND	NVCC_DRAM	VDDARM_IN	VDDARM_IN	VDDARM_IN	VDDARM_IN	VDDARM_IN
DRAM_D25	GND	NVCC_DRAM	VDDSOC_CAP	VDDSOC_CAP	VDDSOC_CAP	GND	GND
DRAM_SDCKE0	GND	NVCC_DRAM	GND	GND	VDDARM_CAP	VDDARM_CAP	VDDARM_CAP
DRAM_A15	GND	NVCC_DRAM	GND	GND	GND	GND	NC
DRAM_A7	GND	NVCC_DRAM	VDDSOC_CAP	VDDSOC_CAP	VDDARM_CAP	VDDARM_CAP	VDDARM_CAP
DRAM_A3	DRAM_A4	NVCC_DRAM	VDDSOC_CAP	VDDSOC_CAP	VDDARM_IN	VDDARM_IN	VDDARM_IN
DRAM_SDBA1	GND	NVCC_DRAM	GND	GND	GND	GND	GND
DRAM_CS0	GND	NVCC_DRAM	VDDSOC_IN	VDDSOC_IN	VDDSOC_IN	VDDSOC_IN	VDDSOC_IN
DRAM_D36	GND	NVCC_DRAM	GND	GND	GND	VDDPU_CAP	VDDPU_CAP
DRAM_D37	GND	NVCC_DRAM	NVCC_DRAM	NVCC_DRAM	NVCC_DRAM	GND	GND
DRAM_D40	GND	GND	GND	GND	NVCC_ENET	NVCC_LCD	DI0_DISP_CLK
DRAM_D44	ENET_TXD1	ENET_MDC	ENET_TXD0	DISP0_DAT21	DISP0_DAT13	DISP0_DAT4	DI0_PIN3
DRAM_DQM7	ENET_RXD0	ENET_TX_EN	ENET_CRS_DV	DISP0_DAT16	DISP0_DAT10	DISP0_DAT3	DI0_PIN15
DRAM_D59	ENET_RXD1	ENET_REF_CLK	DISP0_DAT20	DISP0_DAT15	DISP0_DAT8	DISP0_DAT1	EIM_BCLK
DRAM_D62	ENET_RX_ER	ENET_MDIO	DISP0_DAT19	DISP0_DAT11	DISP0_DAT6	DISP0_DAT2	EIM_DA14
GND	DISP0_DAT23	DISP0_DAT22	DISP0_DAT17	DISP0_DAT12	DISP0_DAT7	DISP0_DAT0	EIM_DA15
DRAM_D58	DRAM_D63	DISP0_DAT18	DISP0_DAT14	DISP0_DAT9	DISP0_DAT5	DI0_PIN4	DI0_PIN2
Y	W	V	U	T	R	P	N